



100V 30mΩ N-Ch Power MOSFET

Features

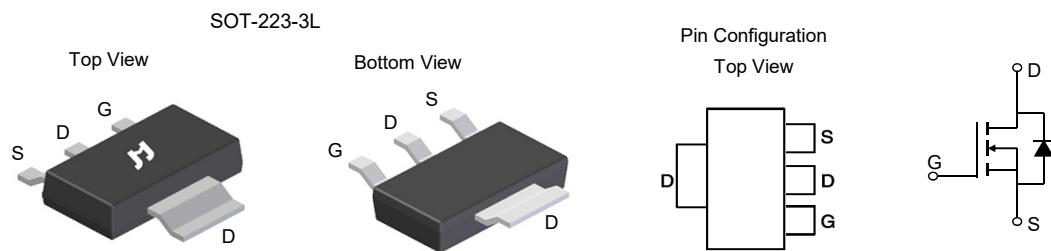
- Low Gate Charge
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

Applications

- Power Management in Computing, CE, IE 4.0, Communications
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Load Switching, Quick/Wireless Charging, Motor Driving

Product Summary

Parameter	Value	Unit
V _{DS}	100	V
V _{GS(th)_Typ}	2.0	V
I _D (@ V _{GS} = 10V) ⁽¹⁾	13	A
R _{DS(ON)_Typ} (@ V _{GS} = 10V)	30	mΩ
R _{DS(ON)_Typ} (@ V _{GS} = 4.5V)	38	mΩ

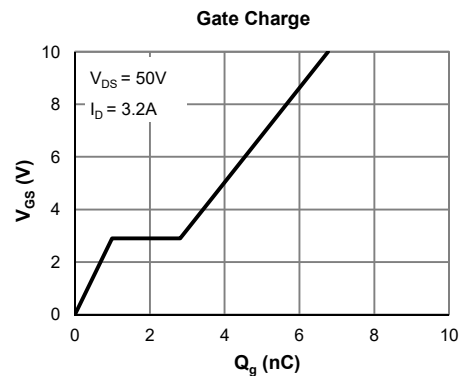
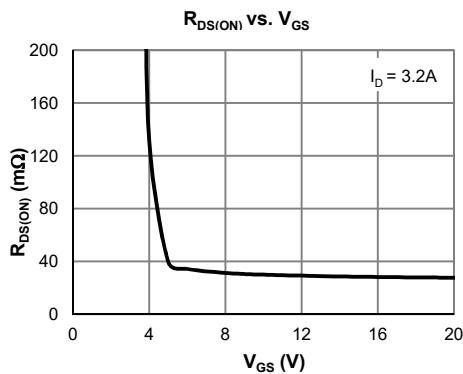


Ordering Information

Device	Package	# of Pins	Marking	MSL	T _J (°C)	Media	Quantity (pcs)
JMSL1040AY-13	SOT-223-3L	3	SL1040A	3	-55 to 150	13-inch Reel	4000

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DS}	100	V
Gate-to-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I _D	T _C = 25°C	13
		T _C = 100°C	8.4
Pulsed Drain Current ⁽²⁾	I _{DM}	48	A
Avalanche Current ⁽³⁾	I _{AS}	6.5	A
Avalanche Energy ⁽³⁾	E _{AS}	21	mJ
Power Dissipation ⁽⁴⁾	P _D	T _C = 25°C	13
		T _C = 100°C	5.1
Junction & Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C



**Electrical Characteristics** (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

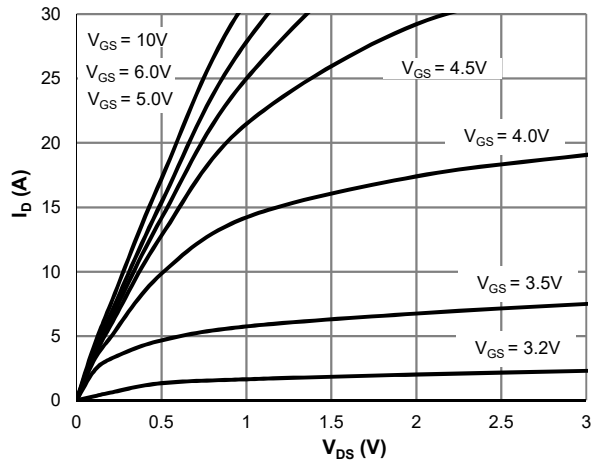
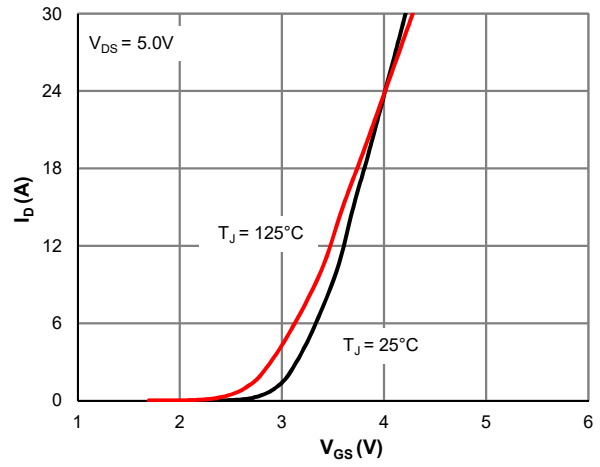
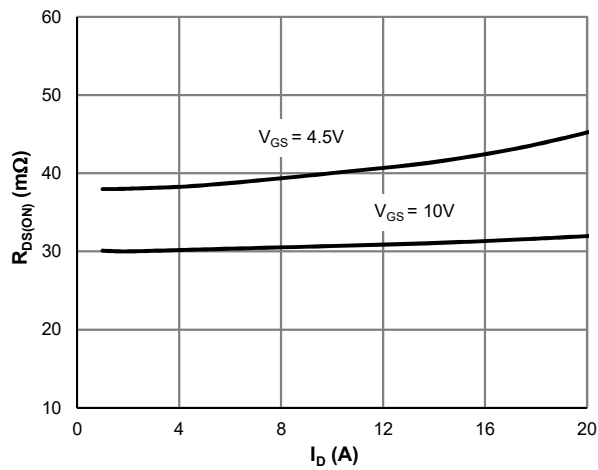
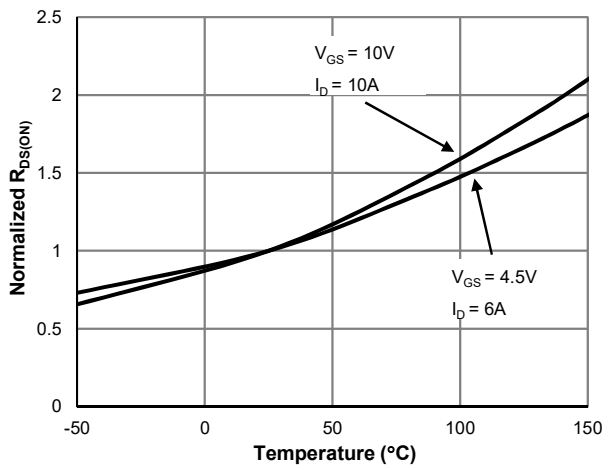
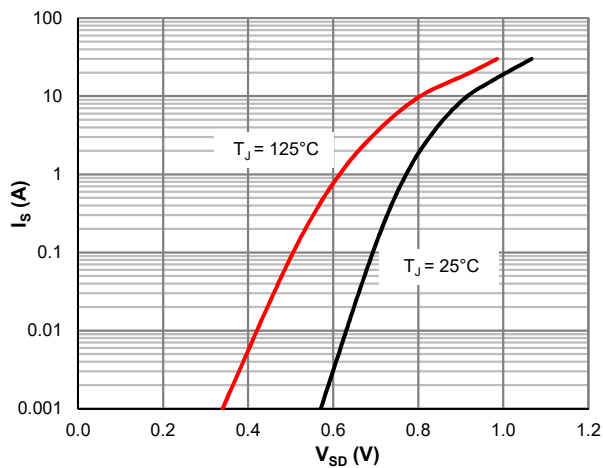
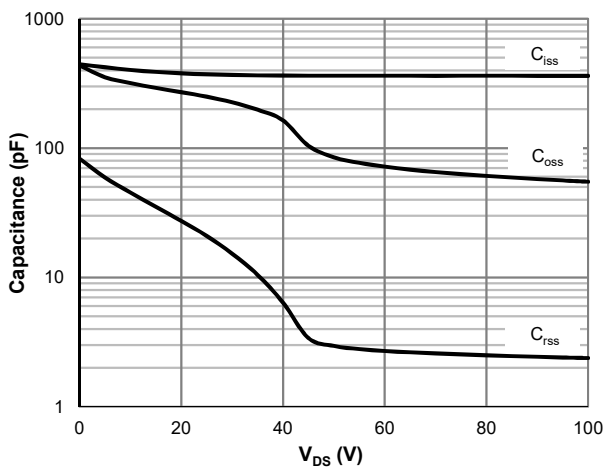
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1.2	2.0	3.0	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 3.2\text{A}$		30	39	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}$, $I_D = 2.7\text{A}$		38	50	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}$, $I_D = 3.2\text{A}$		11		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}$, $V_{GS} = 0\text{V}$		0.70	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			13	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 50\text{V}$, $f = 1\text{MHz}$		363		pF
Output Capacitance	C_{oss}			85		pF
Reverse Transfer Capacitance	C_{rss}			3.0		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$		2.6		Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0$ to 10V $V_{DS} = 50\text{V}$, $I_D = 3.2\text{A}$		6.8		nC
Total Gate Charge (@ $V_{GS} = 4.5\text{V}$)	Q_g			3.7		nC
Gate Source Charge	Q_{gs}			1.0		nC
Gate Drain Charge	Q_{gd}			1.8		nC
Turn-On Delay Time	$t_{D(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 50\text{V}$ $R_L = 15.6\Omega$, $R_{GEN} = 6\Omega$		4.9		ns
Turn-On Rise Time	t_r			16.6		ns
Turn-Off Delay Time	$t_{D(off)}$			11.2		ns
Turn-Off Fall Time	t_f			4.9		ns
Body Diode Reverse Recovery Time	t_{rr}		$I_F = 3.2\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		33	
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 3.2\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		45		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	60	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	7.5	9.8	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [$L = 100\mu\text{H}$, $V_{GS} = 10\text{V}$, $V_{DS} = 50\text{V}$] while its value is limited by $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: Body-Diode Characteristics

Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

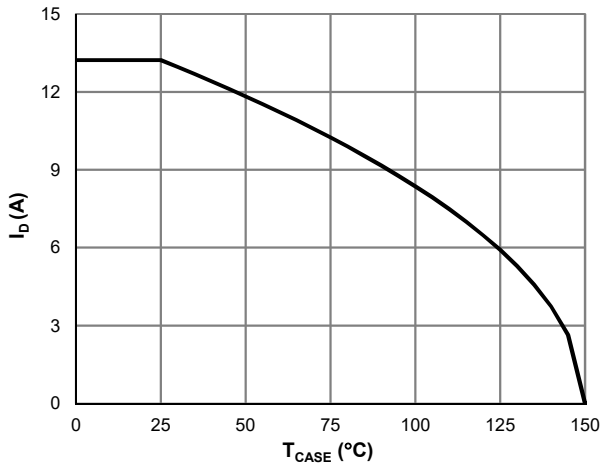


Figure 7: Current De-rating

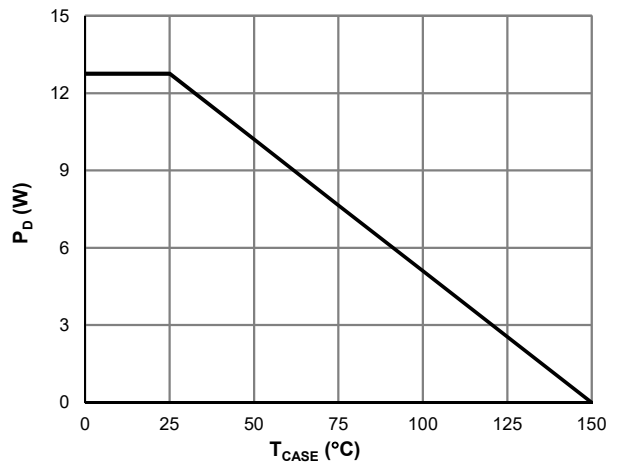


Figure 8: Power De-rating

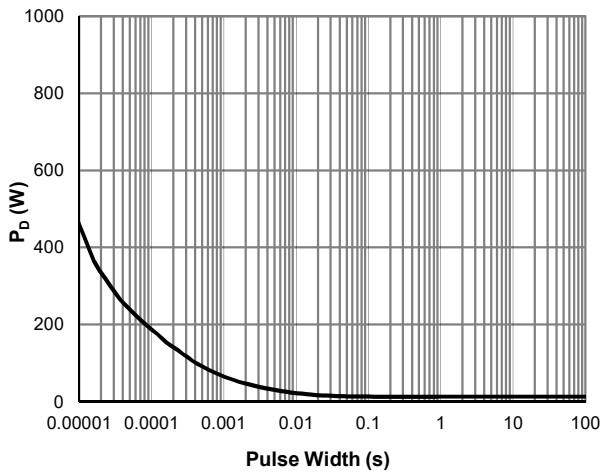
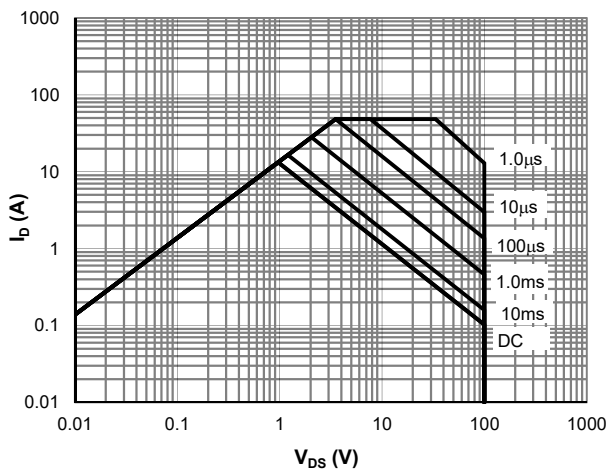


Figure 10: Single Pulse Power Rating, Junction-to-Case

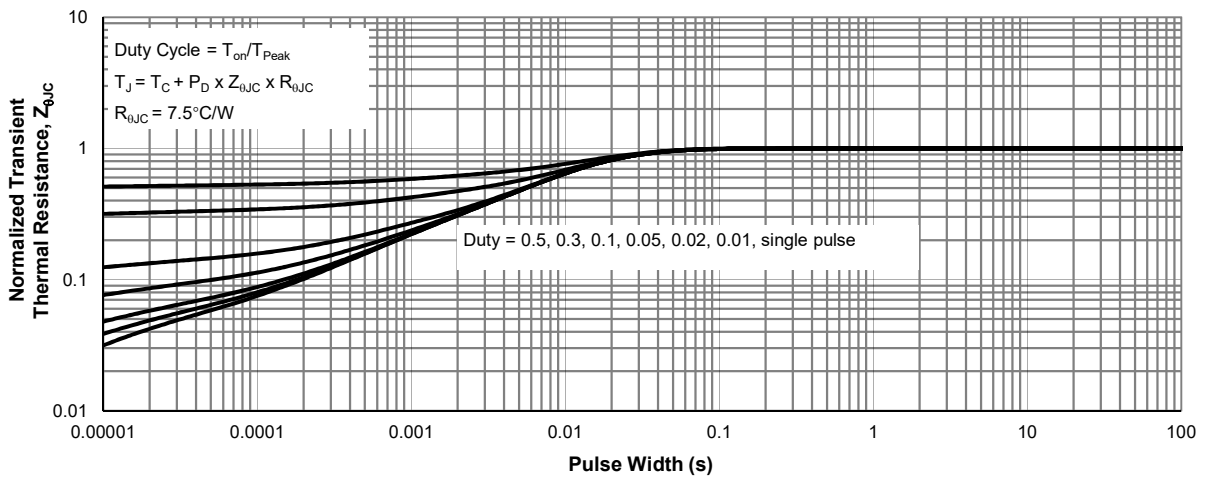
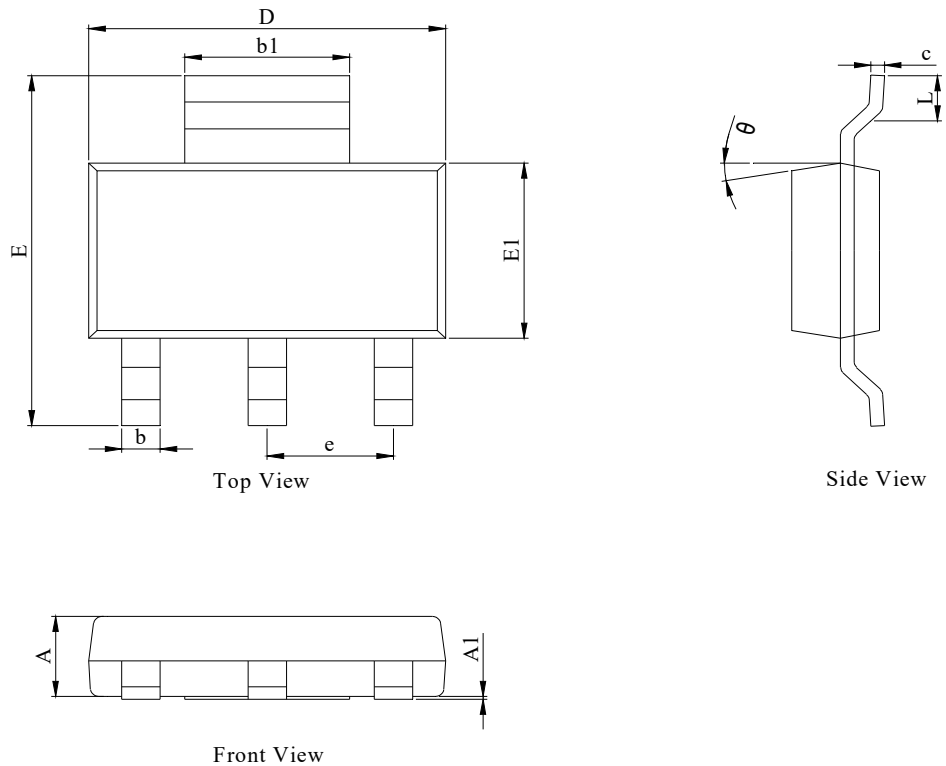
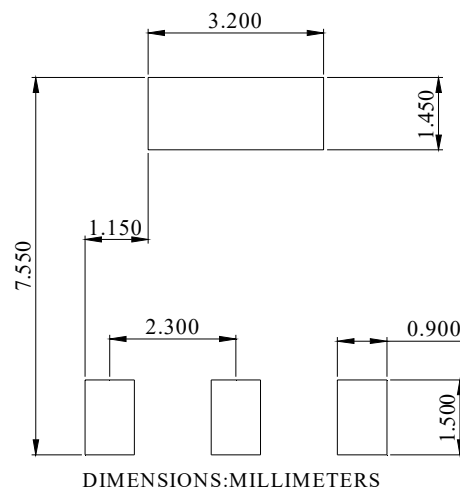


Figure 11: Normalized Maximum Transient Thermal Impedance

SOT-223-3L Package Information
Package Outline


DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	1.50	1.60	1.80
A1	0.01	0.06	0.10
b	0.60	0.70	0.80
b1	2.90	3.00	3.10
D	6.30	6.50	6.70
E	6.70	7.00	7.30
E1	3.30	3.50	3.70
c	0.22	0.26	0.32
L	0.70	0.90	1.10
e	2.30 BSC		
θ	-	-	10°

Recommended Soldering Footprint


单击下面可查看定价，库存，交付和生命周期等信息

[>>JW\(捷捷微\)](#)